



STUDY OF CAESIUM-WALL INTERACTION PARAMETERS WITHIN A HYDROGEN PLASMA

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Extractor and accelerator



SPIDER is the full-size prototype of the negative ion source for the ITER heating neutral beam.

The ITER milestone was met, with first hydrogen plasma discharges in may 2018. The next priorities are Commissioning and integration of diagnostics, ramp up of RF driver performance, replacement of faulty components.

Next, high-current beam operation shall start with the use of caesium vapor.

8x RF drivers





Preparation to the use of caesium in SPIDER

Use of Cs in the ion source













H⁻ scattering from a MoCs surface: *Ab initio* Molecular Dynamics calculations





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8x RF drivers



Aim of this work:

- Review of phenomena influencing Cs adsorption and desorption in a hydrogen plasma discharge
- Collect the data concerning the specificity of SPIDER design
- Identify the principal contributions to the many phenomena involved
 (SPIDER is a very complex and very «rigid» device, we cannot explore the complete space of parameters looking for an influence on caesium effect)



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Purpose of this study is not to find answers, but to find the correct questions!

OUTLINE

3



1 Surface processes concerning Cs ads/desorption Γ_{des}

$$\Gamma_{des,Cs} = \Gamma_{th}(T_w) + \Gamma_{sput}^{(+)} + \Gamma_{sput}^{(BSI)}$$

- Sputtering low/energy high energy
- Thermal desorption
- 2 Transmission probability to plasma bulk
 - Case of SPIDER



 P Sigmund, et al., Phys. Rev. 184 (2), 383 (1969); N Matsunami, et al., Rad, Eff. Lett. S7, 15 (1980); Y Yamamura, et al., Radiat. Eff. Lett 68, 83 (1982)
 M. Wada, et al., Rev Sci Instrum 89, 052103 (2018)
 M Wada, et al., AIP Conf. Proc 1869, 020003 (2017)

Effect of plasma particles: Cs physical sputtering at low energies (<50eV)

- Dependence on binding energy U_B and impact energy E_i is clear in the eq. of sputtering¹⁾ for single-specie target
- To obtain α_N we fitted sputtering yields by Wada ^{2,3} which are given at fixed U_B



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- NOTES:
- 1- Minimum energy for Cs sputtering by D (~20eV)
- 2- Minimum fractional coverage θ below which sputtering by deuterium seems uneffective







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Sputtering yield Y TRIM calculation for a single closedpacked Cs layer on a Mo thick wall

- Cs binding energy of 0.8eV for closely-packed monolayer, Mo atom displacement energy of 34eV for bulk Mo.
- Calculations for a Cs coverage of 20 monolayers showed slightly lower yield per amu, but identical asymptotic behavior at relatively high energies.
- Mo sputtering yield is one order of magnitude less





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ISSUE:

- DOES NOT CONSIDER INTEGRATED DAMAGES AT THE MICROSCALE

Thermal desorption, and adsorption



- At converter: partial coverage → modified Langmuir isotherm. (or Temkin) linear decrease of desorption energy following Fedorus²⁾
- Other surfaces: Transition state theory as a generalization of desorption proc., B.E.T. theory for multilayer adsorption, condensation...



If we use this flux for all surfaces → steady state, only 6min eq. of Cs evaporation is kept in the source! → does not describe reality





Diagnostics:

- Cs evap rate: SID at oven
 nozzle
- Cs density: movable SID
- Cs line integr density: LAS
- Cs sticking: QCM and TC



Temperature Programmed Desorption in CATS (preliminary)



• TPD gives information about rate of desorption, kinetic order of desorption, Energy of desorption... measurement in CATS and interpretation following 1st order desorption analysis by Redhead¹:





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similar spectra and desorption energies found in literature, with simultanous desorption of Cs₂O, Cs₂O zero order desorption energy 1.2eV ²



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 P. A. Redhead, *Vacuum*, **12**, 203-211 (1962)
 C.A. Papageorgopoulos, J.L. Desplat, Surface Science 92 (1980) 119-132.

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- similar spectra and desorption energies found in literature, with simultanous desorption of Cs₂O, Cs₂O zero order desorption energy 1.2eV ²)
- TPD spectra with increasing coverage shared the leading edge; if zero order desorption, Cs desorption energy is approx 1.1 eV
- Cs+Cs2O confirmed by XPS analysis (but air and long time in between)

Thermal desorption, and adsorption





Thermal desorption, and adsorption









Surface processes concerning Cs ads/desorption

2 Transmission probability to plasma bulk

- Velocity of desorbed Cs atoms (phys. sputt. or therm. desorp.)
- Transmission through plasma sheath
- 3 Case of SPIDER



Transmission probability to the plasma bulk





- Sheath model in presence of NI formation at the wall by McAdams¹⁾
- Transmission of **neutral Cs** to the plasma: use test particle of Cs to calculate the overall probability of ionization before reaching V_p , depends on Cs velocity v_z and $n_e(z)$, T_e

R McAdams *et al* 2011 *Plasma Sources Sci. Technol.* **20** 035023
 Eckstein, W., Nucl. Instrum. and Methods in Physics Research B18, 344–348 (1987)

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Thermal desorption: Cs at wall temperature Physical sputtering:
 much higher energy²⁾ (f(E) of Cs particles peaks at desorption energy)





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$V_{s}(V)$		T _{des,Th}	T _{des, sputt}	
20	No NI yield	0.84	0.96	
20	NI yield	0.86	0.97	
10		0.85	0.96	
			<i>n_i=</i> 5.5e17 m ⁻³	

• Immediate recycling back to the wall might affect 15% of thermally desorbed Cs

NOTE:

- TRANSMISSION ANYWAY CLOSE TO UNITY → NOT SO EFFECTIVE COMPARED TO DESORPTION PROCESSES



1 Surface processes concerning Cs ads/desorption

2) Transmission probability to plasma bulk

3 Case of SPIDER





• contributions to Cs desorption flux:

$$\Gamma_{des} = \underline{\Gamma_{th}(T_w)} + \underline{\Gamma_{sput}^{(D^+)}} + \underline{\Gamma_{sput}^{(Cs^+)}} + \underline{\Gamma_{sput}^{(X^+)}}$$



Cs fractional coverage



• contributions to Cs desorption flux:

 $\Gamma_{des} = \Gamma_{th}(T_w) + \Gamma_{sput}^{(D^+)} + \Gamma_{sput}^{(Cs^+)} + \Gamma_{sput}^{(X^+)}$

• Try comparison with local incoming flux: (first order adsorption $s=s_0(1-\theta)$, negligible incoming_neutrals)

$$\Gamma_{Cs,ads} = s(\theta)\Gamma_{Cs^+} + s\Gamma_{Cs^0} \approx \frac{s(\theta)0.6 \cdot n_{Cs^+} \left(\frac{2V_0}{m_{Cs}}\right)^2}{2}$$



But this is D plasma! Yet the effect of sputtering is not significant



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TO BE CLARIFIED:

- terms in sputtering yield:
 - angle of impact (E_{sheath} not parallel to $E_{presheath}$)
 - dependence of Y on surface temperature (MD)
 - chemical sputtering
- terms in sticking s₀
 (surface temperature T_w, angle of incidence, impurities)

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At lateral wall, backplate, driver plate during plasma discharge







At lateral wall, backplate, driver plate during plasma discharge





DRIVER

At lateral wall, backplate, driver plate during plasma discharge





• desorption energy *E*_{des}

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89°C

75°C

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At backplate during plasma discharge and beam extraction: physical sputtering due to BSI





Example of stripping & ionization rates along the accelerator

z (m)

Physical sputtering

 Creation of pos. Ions in the electric field of the accelerator, or entering from downstream the accelerator → production of H₂⁺ slightly larger

At backplate during plasma discharge and beam extraction: physical sputtering due to BSI





Physical sputtering

- Creation of pos. ions in the electric field of the accelerator, or entering from downstream the accelerator → production of H₂⁺ slightly larger
- physical sputtering $Y(E_i) \rightarrow D_2^+$ more effective



Example of stripping & ionization rates along the accelerator

Sputtering yield at high energies (TRIM calculations)

At backplate during plasma discharge and beam extraction: physical sputtering due to BSI





Physical sputtering

- Creation of pos. ions in the electric field of the accelerator, or entering from downstream the accelerator → production of H₂⁺ slightly larger
- physical sputtering $Y(E_i) \rightarrow D_2^+$ more effective
- calculation of < Y> from energy spectra of backstreaming H₂⁺ / D₂⁺



Example of stripping & ionization rates along the accelerator

*d*Γ-/*dx* (1/m)

dl/dx (1/m)

Sputtering yield at high energies (TRIM calculations)

IEDF assuming transmission $T_0(z)=1$ (comparison against EAMCC at optim. perv. showed 40% overestimation of the total current)

At backplate during plasma discharge and beam extraction: thermal desorption due to BSI



T_{water,in}=50°C

Thermal submodel of BSI impact position can be done (22x20 mm) to simulate local heating





At backplate during plasma discharge and beam extraction: thermal desorption due to BSI





What is the dependence on the size of the footprint?

At backplate during plasma discharge and beam extraction: thermal desorption due to BSI



At backplate during plasma discharge and beam extraction



- fast BSI: in SPIDER, Cs thermal desorption due to localized heating might have the same order of magnitude of Cs physical sputtering
- probably, sputtering by plasma ions is anyway more effective (and applies to much larger area)





At backplate during plasma discharge and beam extraction

- fast BSI: in SPIDER, Cs thermal desorption due to localized heating might have the same order of magnitude of Cs physical sputtering
- probably, sputtering by plasma ions is anyway more effective (and applies to much larger area)
- Fast BSI in ITER HNB: Cs thermal desorption has huge contribution, Mo surface peak temperature up to 550°C (Γ_{des}~ 10²⁴ m⁻²s⁻¹); (average T is much less maybe about 90-100°C)





SUMMARY



- TPD analysis for Cs compounds seems promising but should be done in ion-source relevant atmosphere to obtain reliable E_{des} (and pre-exponential factor)
- Cs sputtering yields in the 10eV energy range; electric fields in the plasma (presheath) are important for sputtering and for Cs redistribution; question of impurities;
 BSL contribute to Cs redistribution by thermal desorption

BSI contribute to Cs redistribution by thermal desorption rather than physical sputtering;

- Ab initio MD can provide quantitative results, but can be used only to study well «delimited» problems → from experimental observation we get the correct questions to ask
- SPIDER ion source is designed for thermal loads of ITER
 HNB → temperature control very «robust»

estimated contributions to total desorbed Cs







SUMMARY



- TPD analysis for Cs compounds might provide Edes, etc
 - hydrogen atmosphere and/or hydrogen discharge
- MD analysis
 - NI yield
 - Cs sticking at PG (Cs+, Cs+ energy, presence of impurities?)
- In SPIDER temperature-induced effects shall be less than other machines (cooling system designed for the loads of ITER HNB) both without (plasma only) and with beam extraction
- Sputtering seems the main mechanism for Cs redistribution: sputt. yields for D and impurities are key factors
- IEDF at walls: electric fields in the plasma (presheath) are important for sputtering and for Cs redistribution
- OD approach based on averaged quantities might provide overall



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Help from caesium test stand measurements

compounds on the QCM (mass equivalent to tens of

At 48°C, mass increase is equivalent to sticking s=0.09

(using mobile SID to measure Cs flux density in the

Three dimensional growth of Caesium stable

closed-packed Cs layers)

volume and neglecting O mass)







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Help from caesium test stand measurements



• flash desorption carried out to obtain energy of desorption (very preliminary)



- similar spectra and desorption energies found in literature XX, with simultanous desorption of Cs₂O
- Cs₂O zero order desorption energy 1.2eV XX



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- Cs₂O zero order desorption energy 1.2eV XX
- with increasing coverage exhibits a shared leading edge; if zero order desorption, Cs desorption energy is approx 1.1 eV, if first order 1.3 eV...



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Thermal desorption, and adsorption



- At converter: partial coverage → modified Langmuir isotherm. (or Temkin) linear increase of ads energy
- Other surfaces: TST as a generalization of desorption rate , BET theory for multilayer adsorption, condensation ... (ΔH=0.8eV XX)



If we use this flux for all surfaces → steady state, only 6min eq. of Cs evaporation is kept in the source! → does not describe reality





as working hypotheses:

(measurements to be done also in conditions more relevant to the ion source environment)

 $s(T_w = 50^{\circ}C) = 0.09$ $E_{des} = 1.1 - 1.2 \text{eV}$

QCM and TPD measurements

Same 0-D calculation \rightarrow e.g. 27mg/h evaporation in vacuum, ~20mg/h are detained by 50°C surfaces



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Plasma discharge and beam extraction: transmission probability through the sheath

- high Vp, high Te / low Vp, low Te
- low Vp, low Te, w/ NI
- Example of LAS for th desorption & phys sputtering

grafico dello strato	Attenuazione segnale LAS in funzione di z e della f(E) dei desorbiti	Vista delle aperture la che permettono misu diverse posizioni



Energy distribution of sputtered Cs atoms

Perpendicular velocity of Cs atoms depends on the process that caused desorption:

 Energy distribution of the sputtered Cs atoms ¹) caused by D2+ impact or Cs+ impact (in figure, EDF for impact energy of 20eV)

$$f(E) = \frac{E}{(E + U_B)^{3+2m}} cos \left(\frac{\pi}{2} \left(\frac{E}{E'}\right)^4\right)$$

Energy distribution peaked
at binding energy U_B and
extends to infinite
Cutoff to limit the
distribution to the
maximum transferrable
energy $E' = \gamma E_{in}$
(reduced mass γ)



[1] Eckstein, W., Nucl. Instrum. and Methods in Physics Research B18, 344-348 (1987)

